AMENDMENTS TO THE SPECIFICATION

Please replace paragraph **[0041]** with the following amended paragraph:

[0041] The asymmetry of this embodiment can be seen by comparing the total thickness of the first interface junction, 20 nm, with that of the second interface junction, 40 nm. This asymmetry is also seen as the steeper average slope of the leftmost, downward transition in material composition in Figure [[4]] 3 as compared with the less steep average slope of the rightmost, upward transition. Note that the doping concentration of the first interface junction ranges from 2.86E+18 cm-3 to 6.17E+18 cm-3, while that of the second interface junction ranges from 6.65E+17 cm-3 to 1.93E+18 cm-3. The asymmetry in the interface junction thickness and the asymmetry in doping range work together to provide a lower optical absorption and lower electrical resistance than either separately.